TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSV)

2SK2889

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: R_{DS} (ON) = 0.54 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 9.0 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DSS} = 600 \ V)$
- Enhancement-mode $: V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	600	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	10	А	
	Pulse (Note 1)	I _{DP}	40	А	
Drain power dissipatio	n (Tc = 25°C)	PD	100	W	
Single pulse avalanche energy (Note 2)		E _{AS}	363	mJ	
Avalanche current		I _{AR}	10	А	
Repetitive avalanche e	energy (Note 3)	E _{AR}	10	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Thermal Characteristics

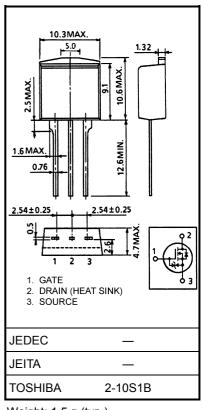
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	1.25	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	83.3	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

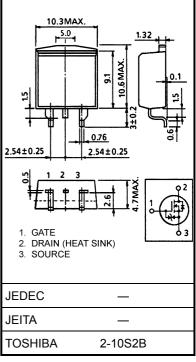
Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 6.36 mH, R_G = 25 Ω ,I_{AR} = 10 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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Unit: mm

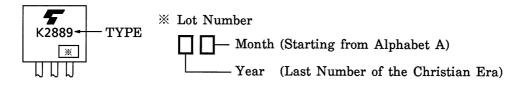
Electrical Characteristics (Ta = 25°C)

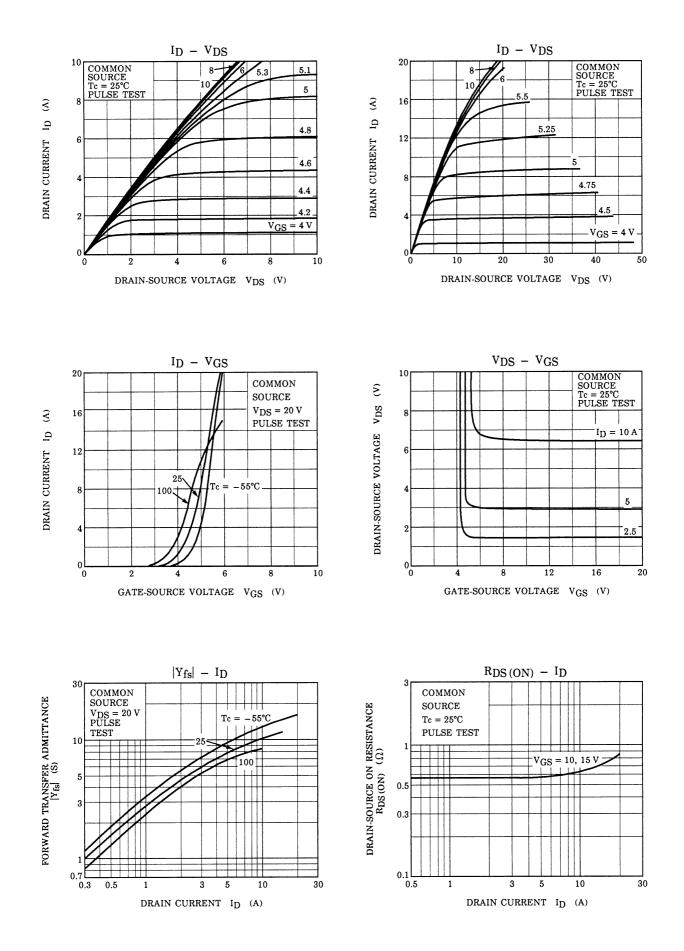
Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V_{GS} = ±25 V, V_{DS} = 0 V	_		±10	μA
Gate-source bro	eakdown voltage	V _(BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 5 A		0.54	0.75	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5 A	3.0	9.0	_	S
Input capacitance	ce	C _{iss}			2040	_	
Reverse transfer capacitance		C _{rss}	_S V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		230	_	pF
Output capacitance		C _{oss}] [590	_	
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{}_{0V} \int_{U} \int$	_	22	_	
	Turn-on time	t _{on}		_	58	_	ns
	Fall time	t _f		_	36	—	115
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w =10 μ s	_	190	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	45	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 10 A		25	_	nC
Gate-drain ("miller") Charge		Q _{gd}			20	—	

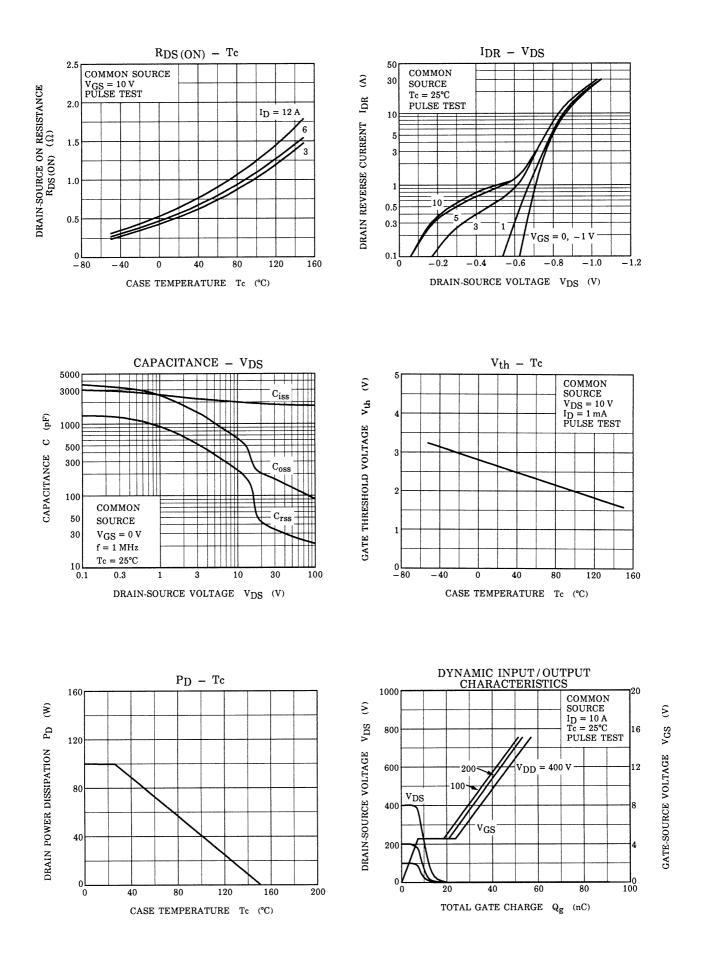
Source–Drain Ratings and Characteristics (Ta = 25°C)

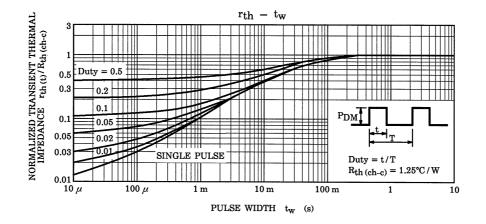
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	10	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	40	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 10 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V		1300	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs	_	16	_	nC

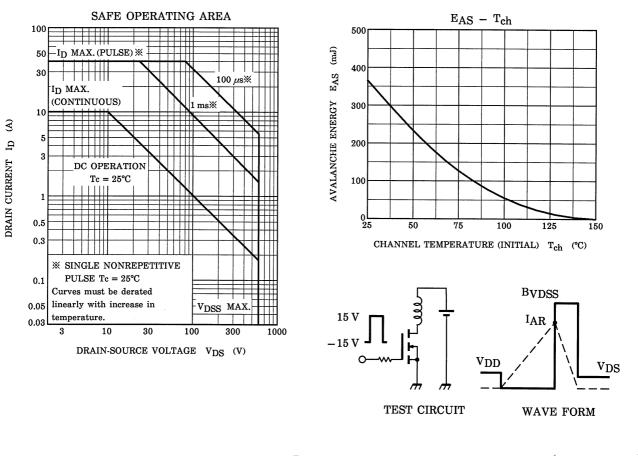
Marking











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